

SCD151N/R.xx



Power Rectifier Diodes

FEATURES

- Diffused diode
- High voltage ratings up to 1600 V
- High surge current capabilities
- Stud cathode and stud anode version
- Hermetic metal case
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see



RoHS
COMPLIANT

TYPICAL APPLICATIONS

- Welders
- Power supplies
- Machine tool controls
- High power drives
- Medium traction applications
- Battery charges
- Freewheeling diodes

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	150 A
Package	DO-8 (DO-205AA)
Circuit configuration	Single

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{F(AV)}$		150	A
	T_c	125	°C
$I_{F(RMS)}$		235	A
I_{FSM}	50 Hz	3000	
	60 Hz	3140	
I^2t	50 Hz	45	kA ² s
	60 Hz	41	
V_{RRM}	Range	400 to 1600	V
T_J		-40 to +180	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
SCD151N/R.xx	04	400	500	15
	08	800	900	
	12	1200	1300	
	16	1600	1700	

FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average forward current at case temperature	$I_{F(AV)}$	180° conduction, half sine wave		150	A	
				125	°C	
Maximum RMS forward current	$I_{F(RMS)}$	DC at 110 °C		235	A	
Maximum peak, one cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum		3000
		t = 8.3 ms				3140
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	45	
		t = 8.3 ms			41	
Slope resistance	r_f	$T_J = T_J$ maximum		0.97	mΩ	
Threshold voltage	$V_{F(T0)}$			0.80	V	
Maximum forward voltage drop	V_{FM}	$I_{pk} = 600$ A, $T_J = 25$ °C, $t_p = 10$ ms sinusoidal wave		1.47		

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction operating and storage temperature range	T_J, T_{Stg}			-40 to +180	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		0.3	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased		0.1	
Maximum allowable mounting torque + 0 - 20 %		Not lubricated threads tightening on hexagon		17	N · m
		Lubricated threads tightening on hexagon		14.5	
		Not lubricated threads tightening on nut		14	
		Lubricated threads tightening on nut		12	
Approximate weight		130 g			
Case style		See dimensions - link at the end of datasheet		DO-8 (DO-205AA)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.031	0.023	$T_J = T_J$ maximum	K/W
120°	0.038	0.040		
90°	0.048	0.053		
60°	0.071	0.075		
30°	0.120	0.121		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

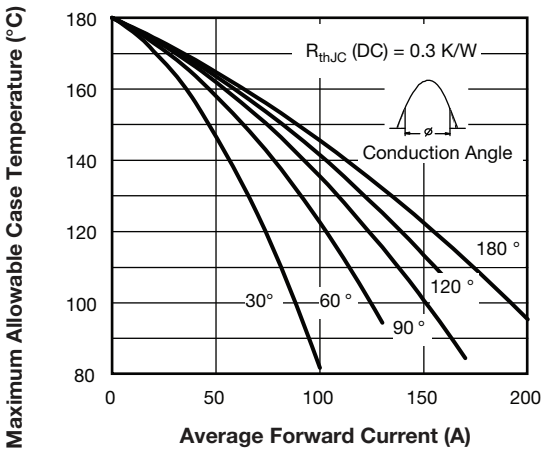


Fig. 1 - Current Ratings Characteristics

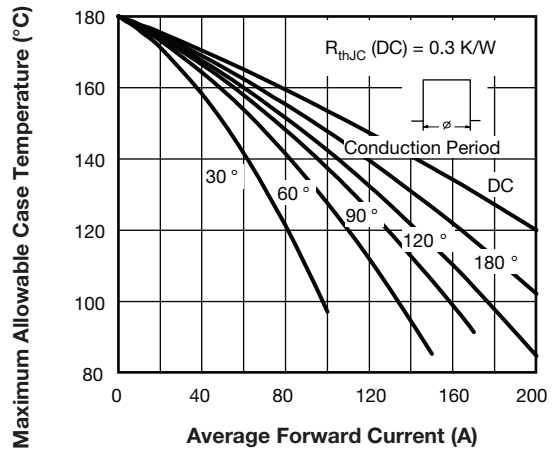


Fig. 2 - Current Ratings Characteristics

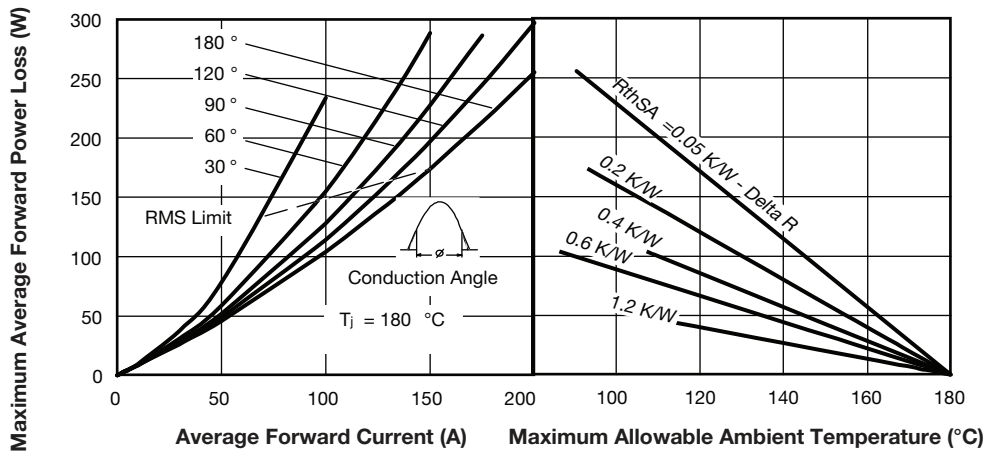


Fig. 3 - Forward Power Loss Characteristics

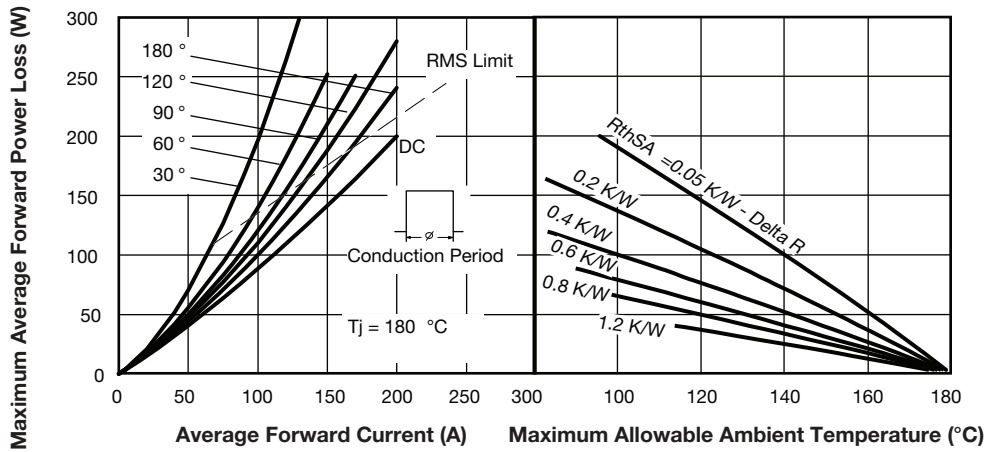


Fig. 4 - Forward Power Loss Characteristics

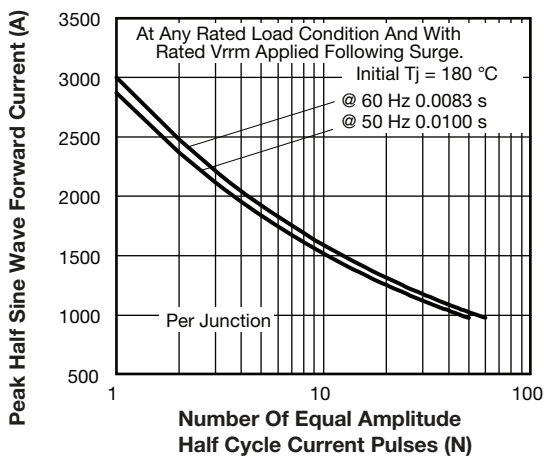


Fig. 5 - Maximum Non-Repetitive Surge Current

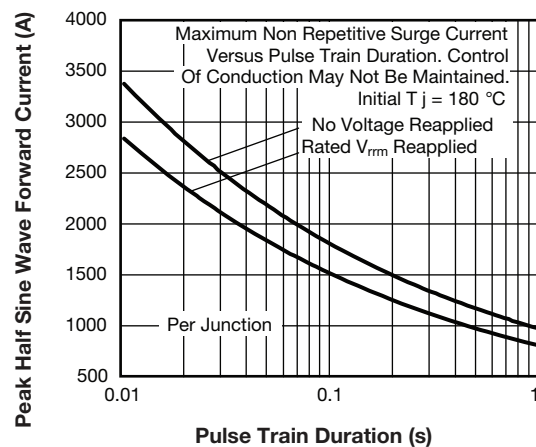


Fig. 6 - Maximum Non-Repetitive Surge Current

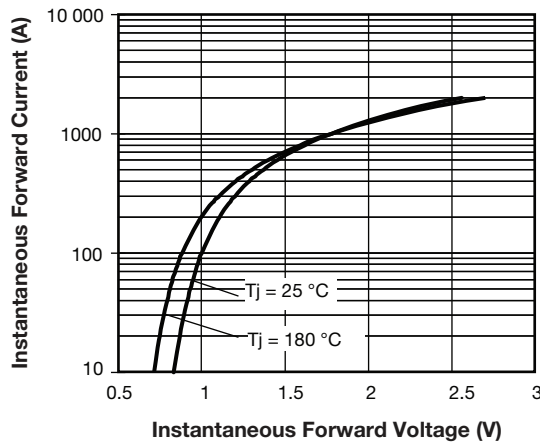


Fig. 7 - Forward Voltage Drop Characteristics

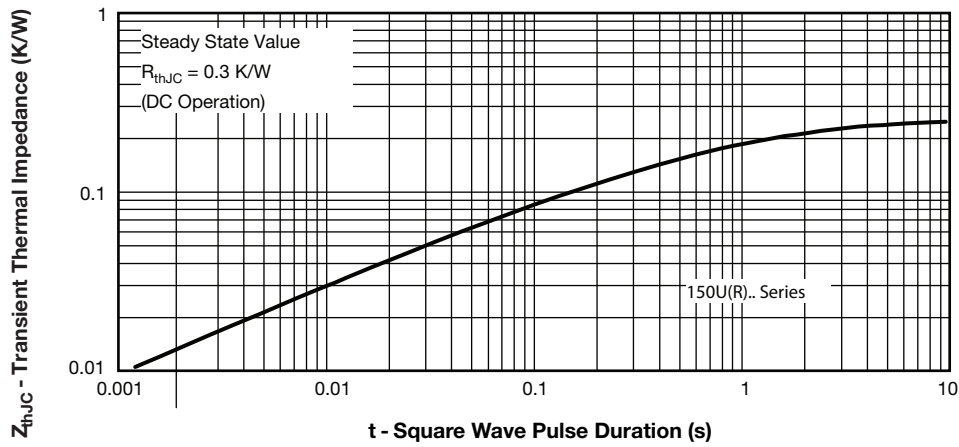
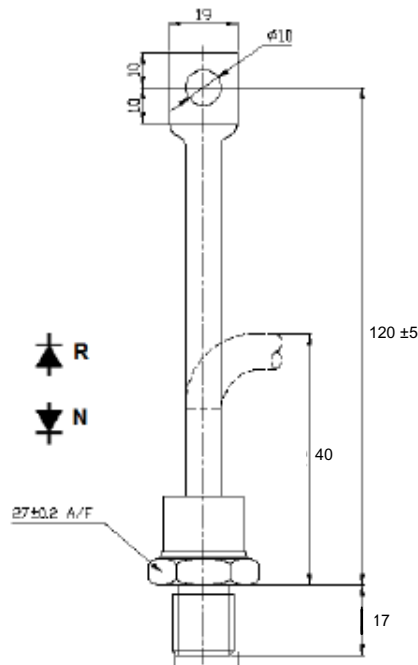


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic



1/2"-20UNF 2A or 3/8"-24UNF 2A
(For metric device M12x1.75)